

Qingyun Xie

List of Publications by Year in descending order

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Version: 2024-02-01

10
papers

365
citations

1478505

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h-index

1872680

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g-index

10
all docs

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docs citations

10
times ranked

279
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Emerging GaN technologies for power, RF, digital, and quantum computing applications: Recent advances and prospects. Journal of Applied Physics, 2021, 130, . | 2.5 | 89 |
| 2 | p-Channel GaN Transistor Based on p-GaN/AlGaIn/GaN on Si. IEEE Electron Device Letters, 2019, 40, 1036-1039. | 3.9 | 88 |
| 3 | Regrowth-Free GaN-Based Complementary Logic on a Si Substrate. IEEE Electron Device Letters, 2020, 41, 820-823. | 3.9 | 74 |
| 4 | First Demonstration of a Self-Aligned GaN p-FET. , 2019, , . | | 25 |
| 5 | Self-Aligned E-Mode GaN <i>p</i> -Channel FinFET With $I_{ON} > 100$ mA/mm and $I_{ON}/I_{OFF} > 10^4$. IEEE Electron Device Letters, 2022, 43, 358-361. | 3.9 | 22 |
| 6 | Field-induced Acceptor Ionization in Enhancement-mode GaN p-MOSFETs. , 2020, , . | | 19 |
| 7 | Tungsten-Gated GaN/AlGaIn <i>p</i> -FET With $I_{sub>max</sub>} > 120$ mA/mm on GaN-on-Si. IEEE Electron Device Letters, 2022, 43, 545-548. | 3.9 | 19 |
| 8 | Effectiveness of oxide trench array as a passive temperature compensation structure in AlN-on-silicon micromechanical resonators. Applied Physics Letters, 2017, 110, . | 3.3 | 15 |
| 9 | A passively temperature-compensated dual-frequency AlN-on-silicon resonator for accurate pressure sensing. , 2017, , . | | 10 |
| 10 | Performance Estimation of GaN CMOS Technology. , 2021, , . | | 4 |